



AMENDMENT UNDER 37 C.F.R. § 1.116
Appln. No.: 10/650,193

Docket No: Q77191

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (previously presented): A semiconductor device comprising:

an insulating underlayer;

a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;

a first silicon-diffused metal layer buried in said groove; and

a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer.

2. (original): The device as set forth in claim 1, wherein said first insulating interlayer comprises at least one of a SiO₂ layer, a SiCN layer, a SiC layer, a SiOC layer and a low-k material layer.

3. (currently amended): ~~The device as set forth in claim 2,~~ A semiconductor device comprising:

an insulating underlayer;

a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;

a first silicon-diffused metal layer buried in said groove; and
a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and
said first insulating interlayer, wherein
said first insulating interlayer comprises at least one of a SiO₂ layer, a SiCN layer, a SiC
layer, a SiOC layer and a low-k material layer and
said low-k material layer comprises one of a ladder-type hydrogen siloxane layer and a
porous ladder-type hydrogen siloxane layer.

4. (original): The device as set forth in claim 3, wherein said ladder-type hydrogen siloxane layer comprises an L-OxTM layer.

5. (original): The device as set forth in claim 3, wherein said ladder-type hydrogen siloxane layer has a density of about 1.50 g/cm³ to 1.58 g/cm³.

6. (original): The device as set forth in claim 3, wherein said ladder-type hydrogen siloxane layer has a refractive index of about 1.38 to 1.40 at a wavelength of about 633 nm.

7. (original): The device as set forth in claim 3, further comprising a mask insulating layer made of silicon dioxide formed on the one of said ladder-type hydrogen siloxane layer and said porous ladder-type hydrogen siloxane layer.

8. (original): The device as set forth in claim 1, wherein said first silicon-diffused metal layer has a larger silicon concentration near an upper side thereof than near a lower side thereof.

9. (original): The device as set forth in claim 1, wherein said first silicon-diffused metal layer comprises a silicon-diffused copper layer.

10. (original): The device as set forth in claim 9, wherein a silicon component of said silicon-diffused copper layer is less than 8 atoms %.

11. (original): The device as set forth in claim 1, wherein said first silicon-diffused metal layer comprises a silicon-diffused copper alloy layer including at least one of Al, Ag, W, Mg, Fe, Ni, Zn, Pd, Cd, Au, Hg, Be, Pt, Zr, Ti and Sn.

12. (previously presented): The device as set forth in claim 1, wherein said first silicon-diffused metal layer includes no metal silicide formed thereon.

13. (original): The device as set forth in claim 1, wherein said first silicon-diffused metal layer includes hydrogen.

14. (canceled).

15. (currently amended): ~~The device as set forth in claim 1,~~ A semiconductor device comprising:

an insulating underlayer;

a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;

a first silicon-diffused metal layer buried in said groove; and

a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer, wherein said first metal diffusion barrier layer comprises at least one of a SiCN layer, a SiC layer, a SiOC layer and an organic material layer.

16. (currently amended): ~~The device as set forth in claim 1, further comprising~~ A semiconductor device comprising:

an insulating underlayer;

a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;

a first silicon-diffused metal layer buried in said groove;

a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer; and

a first etching stopper between said insulating underlayer and said first insulating interlayer.

17. (original): The device as set forth in claim 16, wherein said first etching stopper comprises at least one of a SiCN layer, a SiC layer, a SiOC layer and an organic material layer.

Claims 18-50 (canceled).

51. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- an insulating interlayer formed on said insulating underlayer, said insulating interlayer having a groove;
- a barrier metal layer made of at least one of Ta, TaN, Ti, TiN, TaSiN and TiSiN formed within said groove;
- a silicon-diffused copper layer including no copper silicide formed thereon and and buried in said groove on said barrier metal layer, said silicon-diffused copper layer having a silicon component of less than 8 atoms %; and
- a copper diffusion barrier layer made of at least one of SiCN, SiC, SiOC and organic material and formed on said silicon-diffused copper layer and said insulating interlayer.

Claims 52-212 (canceled).

213. (previously presented): The device as set forth in claim 1, wherein silicon is diffused into the entirety of said first-silicon diffused metal layer.

214. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- an insulating interlayer formed on said insulating under layer, said insulating interlayer having a groove;
- a silicon-diffused metal layer buried in said groove; and
- a metal diffusion barrier layer formed on said silicon-diffused metal layer and said insulating interlayer,

upper surface portions of said insulating interlayer and said silicon-diffused metal layer being nitrided.

215. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;
- a first silicon-diffused metal layer including no carbon therein buried in said groove; and
- a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer,

wherein said first silicon-diffused metal layer has a larger silicon concentration near an upper side thereof than near a lower side thereof.

216. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;
- a first silicon-diffused metal layer including no carbon therein buried in said groove; and
- a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer,

wherein said first metal diffusion barrier layer comprises at least one of a SiCN layer, a SiC layer, a SiOC layer and an organic material layer.

217. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;
- a first silicon-diffused metal layer including no carbon therein buried in said groove; and
- a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer,

further comprising a first etching stopper between said insulating underlayer and said first insulating interlayer.

218. (previously presented): A semiconductor device comprising:

- an insulating underlayer;
- a first insulating interlayer formed on said insulating underlayer, said first insulating interlayer having a groove;
- a first silicon-diffused metal layer including no carbon therein buried in said groove; and
- a first metal diffusion barrier layer formed on said first silicon-diffused metal layer and said first insulating interlayer,

wherein said first etching stopper comprises at least one of a SiCN layer, a SiC layer, a SiOC layer and an organic material layer.